

Application Data Sheet

Application Information

Application Type::	Regular
Subject Matter::	Utility
Suggested Group Art Unit::	N/A
CD-ROM or CD-R?::	None
Sequence submission?::	None
Computer Readable Form (CRF)?::	No
Title::	METHOD FOR N+ DOPING OF AMORPHOUS SILICON AND POLYSILICON ELECTRODES IN DEEP TRENCHES
Attorney Docket Number::	INTECH 3.0-104
Request for Early Publication?::	No
Request for Non-Publication?::	No
Suggested Drawing Figure::	1
Total Drawing Sheets::	6
Small Entity?::	No
Petition included?::	No
Secrecy Order in Parent Appl.?::	No

Applicant Information

Applicant Authority Type::	Inventor
Primary Citizenship Country::	Germany
Status::	Full Capacity
Given Name::	Moritz
Family Name::	Haupt
City of Residence::	Dresden
Country of Residence::	Germany
Street of mailing address::	Am Schulholz 10
City of mailing address::	Dresden

Country of mailing address:: Germany
Postal or Zip Code of mailing address:: D-01109

Correspondence Information

Correspondence Customer Number:: 000530

Representative Information

Representative Customer Number:: 000530

Assignee Information

Assignee name:: Infineon Technologies North America Corp.
Street of mailing address:: 1730 North First Street
City of mailing address:: San Jose
State or Province of mailing address:: CA
Postal or Zip Code of mailing address:: 95112